

**TO-220 Plastic Package**

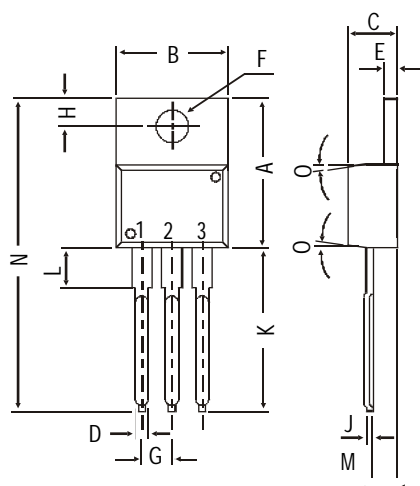
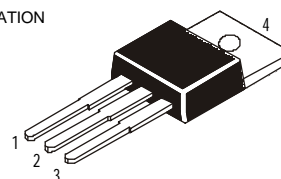
**2N6109**

**2N6109 PNP PLASTIC POWER TRANSISTOR**

*General Purpose Amplifier and Switching Application*

**PIN CONFIGURATION**

1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR



DIM	MIN.	MAX.
A	14.42	16.51
B	9.63	10.67
C	3.56	4.83
D		0.90
E	1.15	1.40
F	3.75	3.88
G	2.29	2.79
H	2.54	3.43
J		0.56
K	12.70	14.73
L	2.80	4.07
M	2.03	2.92
N		31.24
O	DEG 7	

All dimensions in mm.

**ABSOLUTE MAXIMUM RATINGS**

Collector-base voltage (open emitter)

$V_{CBO}$  max. 60 V

Collector-emitter voltage (open base)

$V_{CEO}$  max. 50 V

Collector current

$I_C$  max. 7.0 A

Total power dissipation up to  $T_C = 25^\circ\text{C}$

$P_{tot}$  max. 40 W

Junction temperature

$T_j$  max. 150  $^\circ\text{C}$

Collector-emitter saturation voltage

$V_{CEsat}$  max. 1.0 V

$I_C = 2.5\text{A}; I_B = 0.25\text{A}$

D.C. current gain

$h_{FE}$  min. 30  
max. 150

$I_C = 2.5\text{A}; V_{CE} = 4\text{V}$

**RATINGS** (at  $T_A=25^\circ\text{C}$  unless otherwise specified)

Limiting values

Collector-base voltage (open emitter)

$V_{CBO}$  max. 60 V

Collector-emitter voltage (open base)

$V_{CEO}$  max. 50 V

Emitter-base voltage (open collector)

$V_{EBO}$  max. 5.0 V

Collector current

$I_C$  max. 7.0 A

## 2N6109

Collector current (Peak value)	$I_C$	max.	10 A
Base current	$I_B$	max.	3.0 A
Total power dissipation up to $T_C = 25^\circ\text{C}$	$P_{tot}$	max.	40 W
Derate above $25^\circ\text{C}$		max.	0.32 W/ $^\circ\text{C}$
Junction temperature	$T_j$	max.	150 $^\circ\text{C}$
Storage temperature	$T_{stg}$		-65 to +150 $^\circ\text{C}$

### THERMAL CHARACTERISTICS

From junction to case	$R_{th\ j-c}$		3.125 $^\circ\text{C/W}$
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### CHARACTERISTICS

$T_{amb} = 25^\circ\text{C}$  unless otherwise specified

Collector cutoff current

$I_B = 0$ ;  $V_{CE} = 40\text{V}$

$V_{EB(off)} = 1.5\text{V}$ ;  $V_{CE} = 60\text{V}$

$V_{EB(off)} = 1.5\text{V}$ ;  $V_{CE} = 50\text{V}$ ;  $T_C = 150^\circ\text{C}$

Emitter cut-off current

$I_C = 0$ ;  $V_{EB} = 5\text{V}$

Breakdown voltages

$I_C = 100\text{ mA}$ ;  $I_B = 0$

$I_C = 1\text{ mA}$ ;  $I_E = 0$

$I_E = 1\text{ mA}$ ;  $I_C = 0$

Saturation voltages

$I_C = 2.5\text{ A}$ ;  $I_B = 0.25\text{ A}$

$I_C = 7\text{ A}$ ;  $I_B = 3\text{ A}$

Base emitter on voltages

$I_C = 2.5\text{ A}$ ;  $V_{CE} = 4\text{V}$

$I_C = 7\text{ A}$ ;  $V_{CE} = 4\text{V}$

D.C. current gain

$I_C = 2.5\text{ A}$ ;  $V_{CE} = 4\text{V}$

$I_C = 7\text{ A}$ ;  $V_{CE} = 4\text{V}$

Small-signal current gain  $f = 50\text{ KHz}$

$I_C = 0.5\text{ A}$ ;  $V_{CE} = 4\text{V}$

Output capacitance at  $f = 1\text{ MHz}$

$I_E = 0$ ;  $V_{CB} = 10\text{V}$

Transition frequency at  $f = 1\text{ MHz}$

$I_C = 500\text{ mA}$ ;  $V_{CE} = 4\text{V}$

$I_{CEO}$	max.	1.0 mA
$I_{CEX}$	max.	0.1 mA
$I_{CEX}$	max.	2.0 mA

$I_{EBO}$	max.	1.0 mA
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$V_{CEO(sus)}^*$	min.	50 V
$V_{CBO}$	min.	60 V
$V_{EBO}$	min.	5.0 V

$V_{CEsat}^*$	max.	1.0 V
$V_{CEsat}^*$	max.	3.5 V

$V_{BE(on)}^*$	max.	1.5 V
$V_{BE(on)}^*$	max.	3.0 V

$h_{FE}^*$	min.	30
	max.	150

$h_{FE}^*$	min.	2.3
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$h_{fe}$	min.	20
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$C_o$	max.	250 pF
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$f_T (1)$	min.	10 MHz
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\* Pulse test: pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

(1)  $f_T = |h_{fe}| \cdot f_{test}$

## Notes

### Disclaimer

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